

L Number	Hits	Search Text	DB	Time stamp
1	674	((trench\$2 near isolation) and ((thermal\$2 adj (oxidiz\$3 or oxidation)) or (silicon adj oxynitride) or SiON) and ((silicon adj nitride) or "Si.sub.3N.sub.4" or SiN or Si3N4 or "Si.sub.xN.sub.y")) and 438/424,435,437,981.ccls.	USPAT; US-PGPUB	2004/10/26 18:34
2	14279	trench\$2 near isolation	USPAT; US-PGPUB	2004/10/26 19:30
3	28103	thermal\$2 adj (oxidiz\$3 or oxidation)	USPAT; US-PGPUB	2004/10/26 19:30
4	9676	silicon adj oxynitride	USPAT; US-PGPUB	2004/10/26 19:30
5	11044	SiON	USPAT; US-PGPUB	2004/10/26 19:30
6	81441	silicon adj nitride	USPAT; US-PGPUB	2004/10/26 19:30
7	5928	"Si.sub.3N.sub.4"	USPAT; US-PGPUB	2004/10/26 19:30
8	361	"Si.sub.xN.sub.y"	USPAT; US-PGPUB	2004/10/26 19:31
9	993	Si3N4	USPAT; US-PGPUB	2004/10/26 19:31
10	61971	SiN	USPAT; US-PGPUB	2004/10/26 19:31
11	4189	(trench\$2 near isolation) and (thermal\$2 adj (oxidiz\$3 or oxidation)) and ((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN)	USPAT; US-PGPUB	2004/10/26 19:33
12	17387	compress\$3 adj stress\$2	USPAT; US-PGPUB	2004/10/26 19:32
13	22106	tensile adj stress\$2	USPAT; US-PGPUB	2004/10/26 19:33
14	80	(trench\$2 near isolation) and (thermal\$2 adj (oxidiz\$3 or oxidation)) and (((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN) same ((compress\$3 adj stress\$2) or (tensile adj stress\$2)))	USPAT; US-PGPUB	2004/10/26 20:02
16	51293	trench\$2	USPAT; US-PGPUB	2004/10/26 20:02
17	1696	(trench\$2 near isolation) and ((thermal\$2 adj (oxidiz\$3 or oxidation)) same trench\$2) and (((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN) same trench\$2)	USPAT; US-PGPUB	2004/10/26 20:04
18	657854	deposit\$3	USPAT; US-PGPUB	2004/10/26 20:03
19	1026507	fill\$3	USPAT; US-PGPUB	2004/10/26 20:03
20	1392	(trench\$2 near isolation) and ((thermal\$2 adj (oxidiz\$3 or oxidation)) same trench\$2) and (((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN) same trench\$2 same (deposit\$3 or fill\$3))	USPAT; US-PGPUB	2004/10/26 20:06
21	1613	438/424,435,437.ccls.	USPAT; US-PGPUB	2004/10/26 20:05
22	1233	((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN) and 438/424,435,437.ccls.	USPAT; US-PGPUB	2004/10/26 20:06
23	29	((silicon adj oxynitride) or SiON or (silicon adj nitride) or "Si.sub.3N.sub.4" or "Si.sub.xN.sub.y" or Si3N4 or SiN) same ((compress\$3 adj stress\$2) or (tensile adj stress\$2))) and 438/424,435,437.ccls.	USPAT; US-PGPUB	2004/10/26 20:17